



FUKUCOM COMPANY LTD.

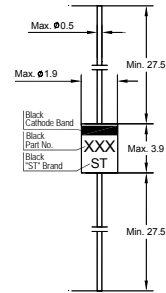
福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

1N4153

SILICON EPITAXIAL PLANAR SWITCHING DIODE



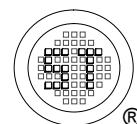
Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1 4	A
	$P_w = 1\text{ s}$ $P_w = 1\text{ }\mu\text{s}$		
Power Dissipation	P_{tot}	500	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Operating Junction temperature	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_S	- 65 to + 200	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Breakdown Voltage at $I_R = 5\text{ }\mu\text{A}$	V_R	75	-	V
Forward Voltage at $I_F = 0.1\text{ mA}$ at $I_F = 0.25\text{ mA}$ at $I_F = 1\text{ mA}$ at $I_F = 2\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 20\text{ mA}$	V_F	0.45 0.49 0.55 0.6 0.69 0.72	0.51 0.55 0.61 0.67 0.76 0.86	V
Reverse Current at $V_R = 50\text{ V}$	I_R	-	50	nA
Total Capacitance at $f = 1\text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$, $I_{rr} = 1\text{ mA}$	t_{rr1}	-	2	ns
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $R_L = 100\text{ }\Omega$, $I_{rr} = 1\text{ mA}$	t_{rr2}	-	4	ns



Dated : 20/06/2007